(19) World Intellectual Property Organization International Bureau



(43) International Publication Date 26 May 2005 (26.05.2005)

PCT

(10) International Publication Number WO 2005/047968 A1

(51) International Patent Classification7: G02F 1/1368, H01L 21/288, 21/3205

(21) International Application Number:

PCT/JP2004/016813

(22) International Filing Date:

5 November 2004 (05.11.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

2003-386030 14 November 2003 (14.11.2003)

(71) Applicant (for all designated States except US): SEMI-CONDUCTOR ENERGY LABORATORY CO., LTD. [JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

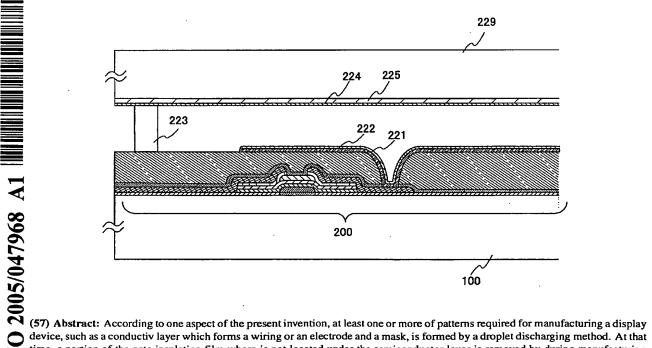
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): FUKUCHI, Kunihiko [JP/JP]; c/o SEMICONDUCTOR ENERGY LAB-ORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa

2430036 (JP). FUJII, Gen [JP/JP]; c/o SEMICONDUC-TOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP). NAKAMURA, Osamu [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP). MAEKAWA, Shinji [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,

[Continued on next page]

(54) Title: DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME



device, such as a conductiv layer which forms a wiring or an electrode and a mask, is formed by a droplet discharging method. At that time, a portion of the gate insulating film where is not located under the semiconductor layer is removed by during manufacturing steps of the present invention.

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ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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